

FCW120D10D1

eSiC Silicon Carbide Schottky Diode

1200V, 10A



Description

The 1200V eSiC is an advanced Faster Semiconductor's silicon carbide diode family. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the eSiC family is suitable for application requiring high power efficiency

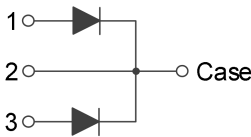
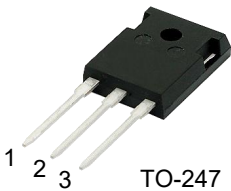
Applications

- Solar inverter, UPS
- EV charging station
- Power Factor Correction

Features (Per Leg/Device)

V_{RRM}	I_F	$T_{J,max}$	Q_C
1200 V	5 / 10 A	175 °C	32 nC

- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature
- Pb-Free, Halogen Free and RoHS compliant



Absolute Maximum Ratings (Per Leg / Device, Per Leg unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_C = 25^{\circ}C$	1200	V
I_F	Forward Current	$T_C = 154^{\circ}C$	5 / 10	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	$T_C = 25^{\circ}C, t_p = 10\text{ ms}$	40	A
		$T_C = 150^{\circ}C, t_p = 10\text{ ms}$	34	A
$I_{F,Max}$	Non-Repetitive Peak Forward Current	$T_C = 25^{\circ}C, t_p = 10\text{ }\mu s$	440	A
		$T_C = 150^{\circ}C, t_p = 10\text{ }\mu s$	370	A
I^2dt value	$\int I^2t$	$T_C = 25^{\circ}C, t_p = 10\text{ ms}$	8	A ² s
		$T_C = 150^{\circ}C, t_p = 10\text{ ms}$	5.8	A ² s
P_{tot}	Power Dissipation	$T_C = 25^{\circ}C$	87	W
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to +175	°C

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. (Per Leg / Device)	1.73 / 0.67	°C/W

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
FCW120D10D1	FCW120D10D1	TO-247	Tube	30 units

Electrical Characteristics (Per Leg, T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F = 5 A, T _C = 25°C		1.39	1.70	V
		I _F = 5 A, T _C = 175°C		1.8	-	
I _R	Reverse Current	V _R = 1200 V, T _C = 25°C		-	100	μA
		V _R = 1200 V, T _C = 175°C		-	300	
Q _C	Total Capacitive Charge	V _R = 800 V, T _C = 25°C		32		nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz		349		pF
		V _R = 800 V, f = 100 kHz		22.7		
E _C	Capacitance Stored Energy	V _R = 800 V, T _C = 25°C		9.2		μJ

Typical Performance Characteristics (Per Leg)

Figure 1. Power Derating

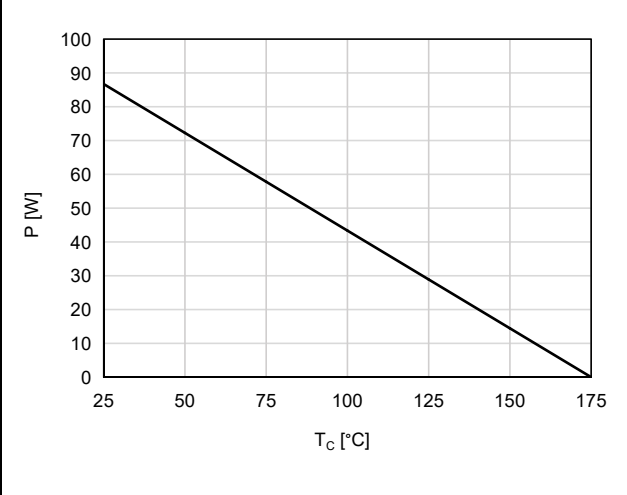


Figure 2. Current Derating

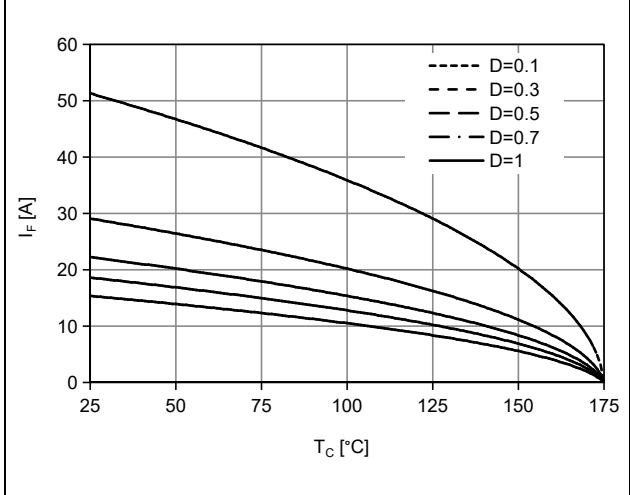


Figure 3. Forward Characteristics

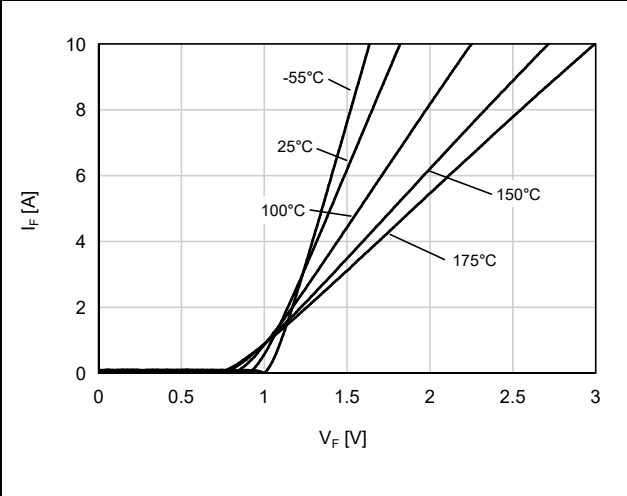


Figure 4. Reverse Characteristics

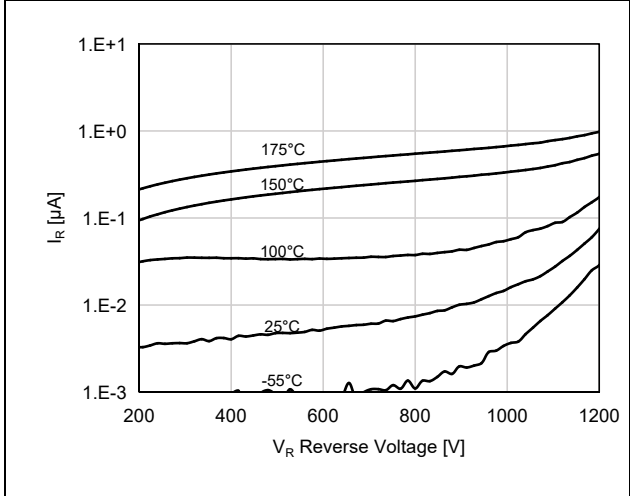


Figure 5. Capacitive Charge Characteristics

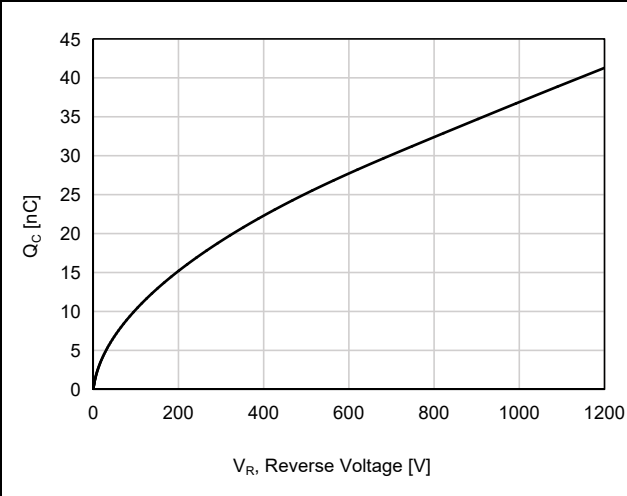
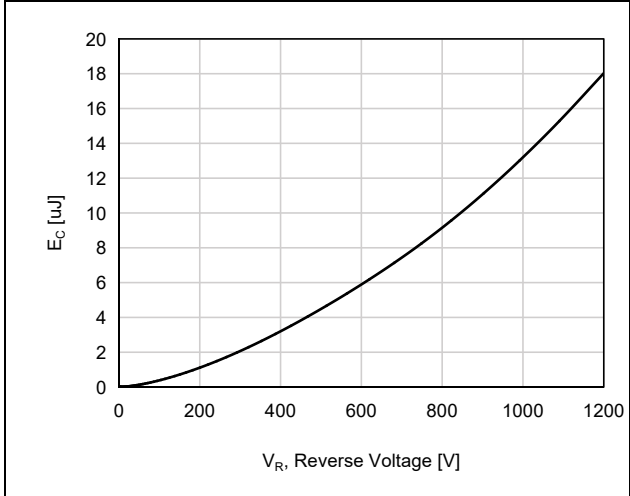


Figure 6. Capacitance Stored Energy



Typical Performance Characteristics (Per Leg)

Figure 7. Capacitance Characteristics

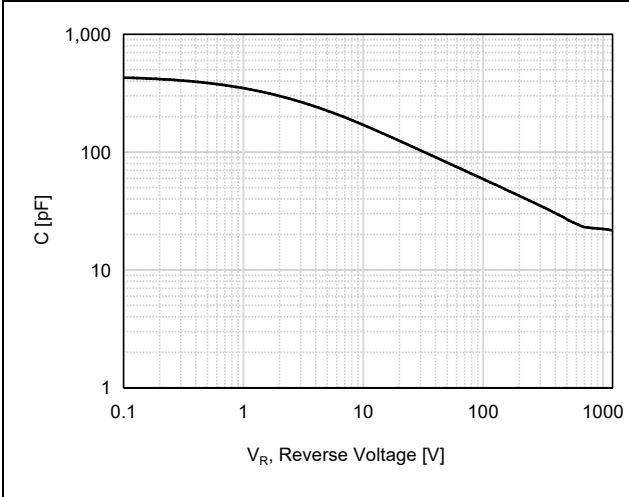
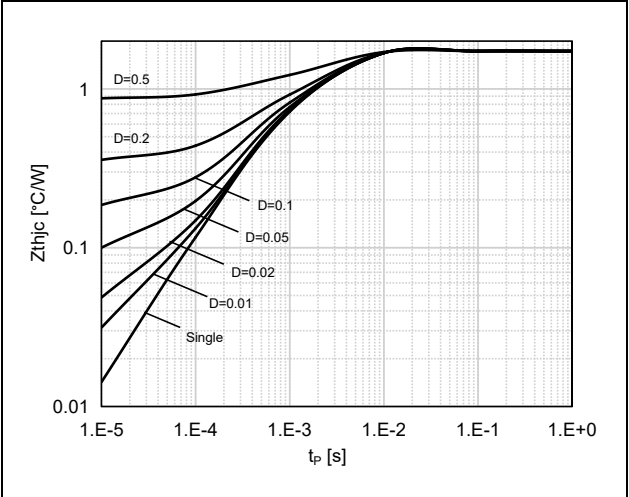
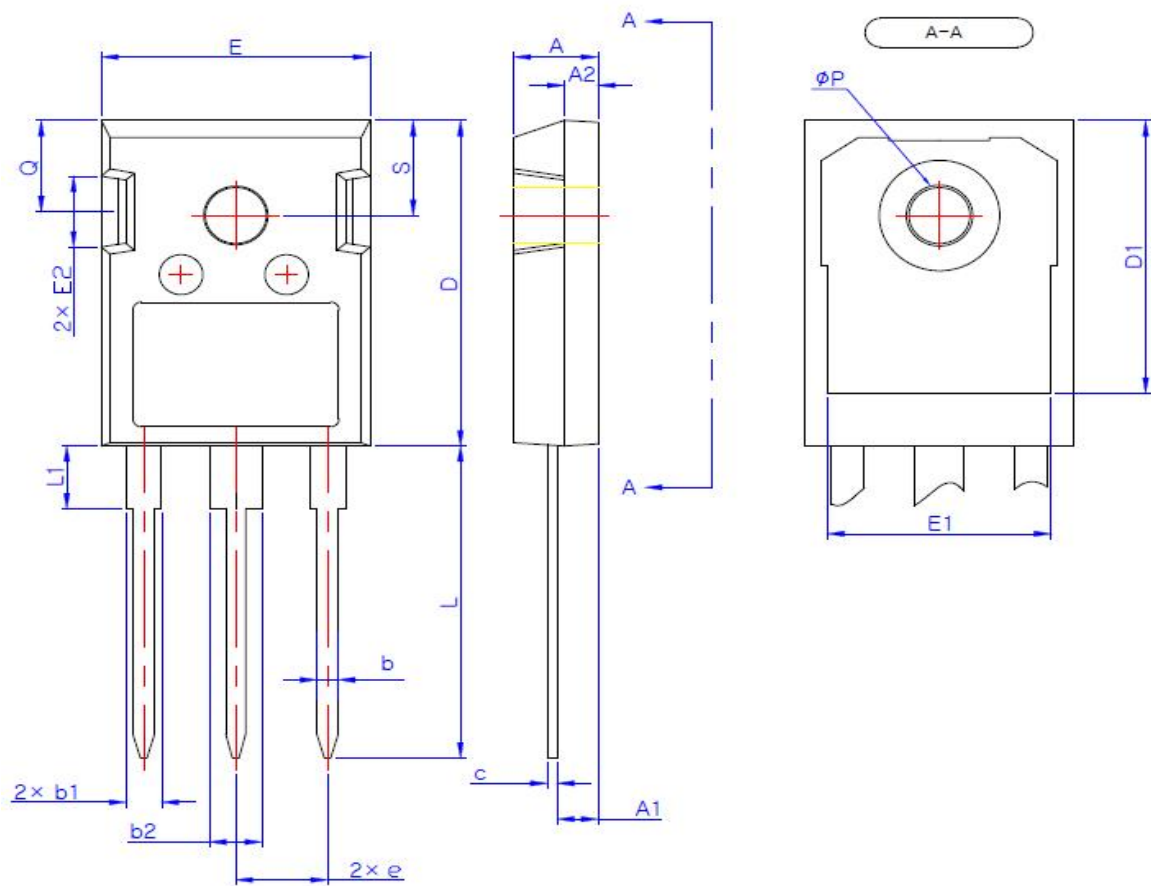


Figure 8. Transient Thermal Response Curve



Package Outlines

TO-247



SYMBOL	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.29	2.42	2.54
A2	1.90	2.00	2.10
b	1.10	1.20	1.30
b1	1.91	2.06	2.20
b2	2.92	3.06	3.20
c	0.50	0.60	0.70
D	20.80	21.07	21.34
D1	17.43	17.63	17.83
E	15.75	15.94	16.13
E1	13.06	13.26	13.46
E2	4.32	4.58	4.83
e	5.45 BSC		
L	19.85	20.05	20.25
L1	4.05	4.27	4.49
ϕP	3.55	3.60	3.65
Q	5.59	5.89	6.19
S	6.15 BSC		

* Dimensions in millimeters